



**AMENDMENTS TO THE CLAIMS:**

Please cancel claims 1 and 9, without prejudice. Kindly amend claims 2, 3 and 10, and add new claims 14 and 15, as shown below.

This listing of claims will replace all prior versions and listings of claims in the Application.

**Claim 1 (canceled)**

**Claim 2 (currently amended):** ~~The semiconductor device according to claim 1, further comprising:~~ A semiconductor device comprising:

a first substrate;

a first heatsink plate connected to said first substrate;

a second substrate having main and rear surfaces, said rear surface of said second substrate being connected to said first heatsink plate;

a semiconductor chip having a main surface bonded to said main surface of said second substrate;

a second heatsink plate connected to a rear surface of said semiconductor chip;

a first pad coupled to a rear surface of said first substrate; and

a second pad coupled to said main surface of said second substrate to be electrically connected to said semiconductor chip,

wherein said first substrate includes a first interconnection therethrough connected to said first pad,

wherein said second substrate includes a second interconnection therethrough connected to said second pad, and

wherein said first heatsink plate includes a via contact providing an electrical connection between said first and second interconnections.

**Claim 3 (currently amended):** The semiconductor device according to claim [[1]] 2, wherein said first heatsink plate includes:

a body portion disposed between said first and second substrates;

a side portion connected to said body portion to form an edge therebetween.

**Claim 4 (original):** The semiconductor device according to claim 3, wherein said side portion is perpendicular to said body portion.

**Claim 5 (original):** The semiconductor device according to claim 3, wherein said first heatsink plate further includes an upper portion connected to said side portion.

**Claim 6 (original):** The semiconductor device according to claim 5, wherein said upper portion is perpendicular to said side portion.

**Claim 7 (original):** The semiconductor device according to claim 5, wherein said second heatsink plate is connected to said upper portion.

**Claim 8 (original):** The semiconductor device according to claim 2, wherein said first and second heatsink plate are connected to each other to form an enclosure around said semiconductor chip.

**Claim 9 (canceled)**

**Claim 10 (currently amended):** ~~The method according to claim 9, further comprising: A~~  
fabrication method of a semiconductor device comprising:

coupling a rear surface of a first heatsink plate to a main surface of a first substrate;

coupling a rear surface of a second substrate to a main surface of said first heatsink

plate;

flipchip bonding a semiconductor chip onto said main surface of said second substrate;

coupling a second heatsink plate to a rear surface of said semiconductor chip;

folding said first heatsink plate on an edge to form body and side portions within said first heatsink plate, said body portion being disposed between said first and second substrates.

**Claim 11 (original):** The method according to claim 10, further comprising:

folding said first heatsink plate on another edge to form upper portions connected to said side portions within said first heatsink plate.

**Claim 12 (original):** The method according to claim 11, further comprising:

coupling said second heatsink plate to said upper portions.

**Claim 13 (original):** The method according to claim 12, wherein said first and second heatsink plates form an enclosure around said semiconductor chip.

**Claim 14 (new):** A semiconductor device comprising:

a first substrate;

a first heatsink plate connected to said first substrate;

a second substrate having main and rear surfaces, said rear surface of said second substrate being connected to said first heatsink plate;

a semiconductor chip having a main surface bonded to said main surface of said second substrate;

a second heatsink plate connected to a rear surface of said semiconductor chip without an insulating substrate of highly thermally conductive material.

**Claim 15 (new):** The semiconductor device according to claim 14, wherein said first heatsink

plate includes:

a body portion disposed between said first and second substrates;

a side portion connected to said body portion to form an edge therebetween.

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